

**2N3043
thru
2N3048**

CASE 610A-04, STYLE 1

**DUAL
AMPLIFIER TRANSISTOR**

NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V _{CEO}	45		Vdc
Collector-Base Voltage	V _{CBO}	45		Vdc
Emitter-Base Voltage	V _{EBO}	5.0		Vdc
Collector Current — Continuous	I _C	30		mAdc
		One Die		Both Die
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	250 1.67	350 2.33	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	0.7 4.67	1.4 9.33	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	45	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current (V _{CB} = 45 Vdc, I _E = 0) (V _{CB} = 45 Vdc, I _E = 0, T _A = +150°C)	I _{CBO}	— —	0.010 10	μAdc
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	—	0.010	μAdc
ON CHARACTERISTICS				
DC Current Gain(1) (I _C = 10 μAdc, V _{CE} = 5.0 Vdc)	h _{FE}	100 50	300 200	—
(I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)		130 65	— —	—
Collector-Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 0.5 mAdc)	V _{CE(sat)}	—	1.0	Vdc
Base-Emitter On Voltage (I _C = 10 mAdc, V _{CE} = 5.0 Vdc)	V _{BE}	0.6	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain — Bandwidth Product (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 20 MHz)	f _T	30	—	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	—	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{ie}	3.2k 1.6k	19k 13k	Ohms
Small-Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)		130 65	600 400	—
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	h _{oe}	— —	100 70	μhos
Noise Figure (I _C = 10 μAdc, V _{CE} = 5.0 Vdc, R _S = 10 kohms, Bandwidth = 10 Hz to 15.7 kHz)	NF	—	5.0	dB

2N3043 thru 2N3048

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
MATCHING CHARACTERISTICS				
DC Current Gain Ratio(2) ($I_C = 10 \mu\text{A}_{\text{dc}}$, $V_{CE} = 5.0 \text{ Vdc}$) 2N3043, 2N3046 2N3044, 2N3047	h_{FE1}/h_{FE2}	0.9 0.8	1.0 1.0	—
Base-Emitter Voltage Differential ($I_C = 10 \mu\text{A}_{\text{dc}}$, $V_{CE} = 5.0 \text{ Vdc}$) 2N3043, 2N3046 2N3044, 2N3047	$ V_{BE1}-V_{BE2} $	— —	5.0 10	mVdc
Base-Emitter Voltage Differential Temperature Gradient ($I_C = 10 \mu\text{A}_{\text{dc}}$, $V_{CE} = 5.0 \text{ Vdc}$, $T_A = -55$ to $+125^\circ\text{C}$) 2N3043, 2N3046 2N3044, 2N3047	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	— —	10 20	$\mu\text{V}^\circ\text{C}$

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

(2) The lowest h_{FE} reading is taken as h_{FE1} for this test.